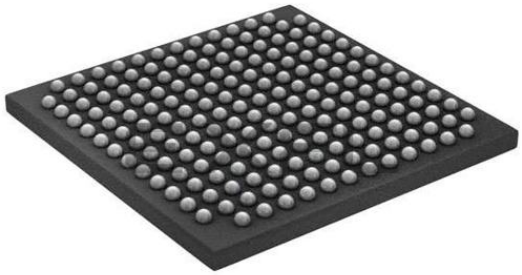


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	200MHz
Connectivity	CANbus, CSIO, EBI/EMI, I²C, LINbus, SD, SPI, UART/USART
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	152
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 32x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	192-LFBGA
Supplier Device Package	192-FBGA (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/s6e2c4aj0agb1000a

Multi-function Serial Interface (Max 16 channels)

- Separate 64 byte receive and transmit FIFO buffers for channels 0 to 7.
- Operation mode is selectable for each channel from the following:
  - UART
  - CSIO (SPI)
  - LIN
  - I^2C
- UART
  - Full-duplex double buffer
  - Selection with or without parity supported
  - Built-in dedicated baud rate generator
  - External clock available as a serial clock
  - Various error detect functions available (parity errors, framing errors, and overrun errors)
- CSIO (SPI)
  - Full-duplex double buffer
  - Built-in dedicated baud rate generator
  - Overrun error detect function available
  - Serial chip select function (ch 6 and ch 7 only)
  - Supports high-speed SPI (ch 4 and ch 6 only)
  - Data length 5 to 16-bit
- LIN
  - LIN protocol Rev.2.1 supported
  - Full-duplex double buffer
  - Master/slave mode supported
  - LIN break field generation (can change to 13- to 16-bit length)
  - LIN break delimiter generation (can change to 1- to 4-bit length)
  - Various error detect functions available (parity errors, framing errors, and overrun errors)
- I^2C
  - Standard mode (Max 100 kbps)/Fast mode (Max 400 kbps) supported
  - Fast mode Plus (Fm+) (Max 1000 kbps, only for ch 3 = ch A and ch 7 = ch B) supported

DMA Controller (Eight channels)

DMA controller has an independent bus, so the CPU and DMA controller can process simultaneously.

- Eight independently configured and operated channels
- Transfer can be started by software or request from the built-in peripherals
- Transfer address area: 32-bit (4 GB)
- Transfer mode: Block transfer/Burst transfer/Demand transfer
- Transfer data type: bytes/half-word/word
- Transfer block count: 1 to 16
- Number of transfers: 1 to 65536

DSTC (Descriptor System data Transfer Controller; 256 Channels)

The DSTC can transfer data at high-speed without going via the CPU. The DSTC adopts the descriptor system and, following the specified contents of the descriptor that has already been constructed on the memory, can access directly the memory/peripheral device and perform the data-transfer operation.

It supports the software activation, the hardware activation, and the chain activation functions.

A/D Converter (Max 32 channels)

- 12-bit A/D Converter
  - Successive approximation type
  - Built-in three units
  - Conversion time: 0.5 µs at 5 V
  - Priority conversion available (priority at two levels)
  - Scanning conversion mode
  - Built-in FIFO for conversion data storage (for SCAN conversion: 16 steps, for priority conversion: 4 steps)

D/A Converter (Max 2 Channels)

- R-2R type
- 12-bit resolution

Base Timer (Max 16 Channels)

Operation mode is selected from the following for each channel:

- 16-bit PWM timer
- 16-bit PPG timer
- 16-/32-bit reload timer
- 16-/32-bit PWC timer

General Purpose I/O Port

This series can use its pins as general purpose I/O ports when they are not used for external bus or peripherals; moreover, the port relocate function is built in. It can set the I/O port to which the peripheral function can be allocated.

- Capable of pull-up control per pin
- Capable of reading pin level directly
- Built-in port-relocate function
- Up to 120 high-speed general-purpose I/O ports in 144 pin package
- Some pins 5V tolerant I/O.
  See 4. Pin Descriptions and 5. I/O Circuit Type for the corresponding pins.

Programmable Cyclic Redundancy Check (PRGCRC) Accelerator

The CRC accelerator helps a verify data transmission or storage integrity.

CCITT CRC16, IEEE-802.3 CRC32 and generating polynomial are supported.

- CCITT CRC16 generator polynomial: 0x1021
- IEEE-802.3 CRC32 generator polynomial: 0x04C11DB7
- Generating polynomial

SD Card Interface

It is possible to use the SD card that conforms to the following standards.

- Part 1 Physical Layer Specification version 3.01
- Part E1 SDIO Specification version 3.00
- Part A2 SD Host Controller Standard Specification version 3.00
- 1-bit or 4-bit data bus

I²S (Inter-IC Sound Bus) Interface (TX x 1 channel, RX x 1 channel)

- Supports three transfer protocols
  - I²S
  - Left justified
  - DSP mode
  - Separate clock generation block for flexible system integration options
- Master/slave mode selectable
- RX Only, TX Only or TX and RX simultaneous operation selectable
- Word length is programmable from 7-bits to 32 bits
- RX/TX FIFO integrated (RX: 66 words x 32-bits, TX: 66 words x 32-bits)
- DMA, interrupts, or polling based data transfer supported

High-Speed Quad SPI

Up to 66 MHz clock rates for very fast data transfers to and from SPI compatible devices.

Up to 256 Mbytes of memory mapped address space.

- Single data rate (SDR)
- Supports single, dual, and quad data modes
- Built-in direct mode and command sequencer mode
  - Direct mode: Access by use of transmission FIFO/reception FIFO (up to16 word x 32 bit)
  - Command sequencer mode: Automatic access assigned to external device area.

Clock and Reset

- Clocks

Five clock sources (two external oscillators, two internal CR oscillators, and Main PLL) that are dynamically selectable.

  - Main clock: 4 MHz to 48 MHz
  - Sub clock: 32.768 kHz
  - High-speed internal CR clock: 4 MHz
  - Low-speed internal CR clock: 100 kHz
  - Main PLL Clock

- Resets
  - Reset requests from INITX pin
  - Power on reset
  - Software reset
  - Watchdog timer reset
  - Low-voltage detector reset
  - Clock supervisor reset

Clock Supervisor (CSV)

Clocks generated by internal CR oscillators are used to supervise abnormality of the external clocks.

- External OSC clock failure (clock stop) is detected, reset is asserted.
- External OSC frequency anomaly is detected, interrupt or reset is asserted.

Low-Voltage Detector (LVD)

This Series include two-stage monitoring of voltage on the VCC pins. When the voltage falls below the voltage that has been set, the low-voltage detector function generates an interrupt or reset.

- LVD1: error reporting via interrupt
- LVD2: auto-reset operation

Low-power Consumption Mode

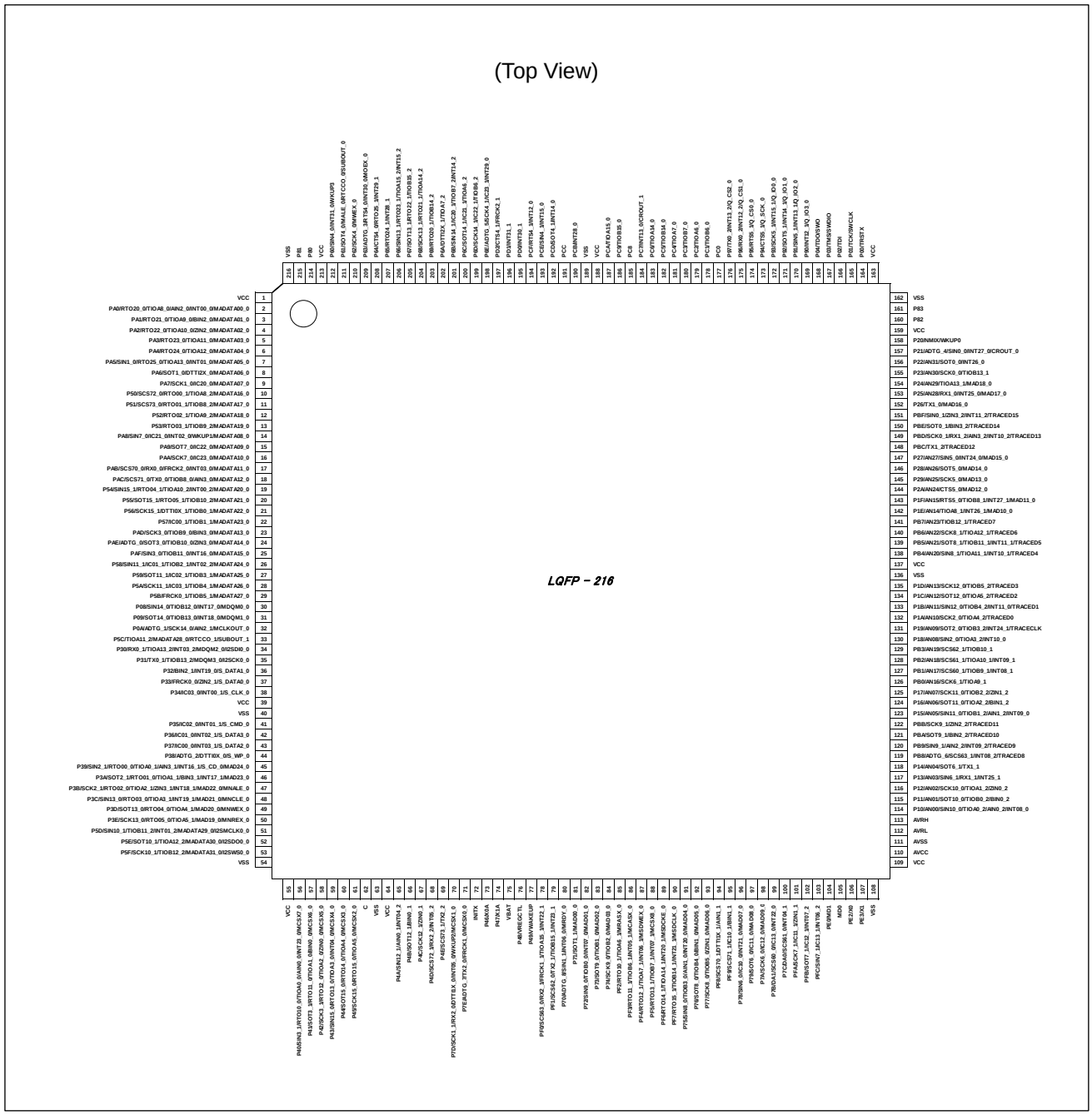
Six low power consumption modes are supported.

- Sleep
- Timer
- RTC
- Stop
- Deep standby RTC (selectable from with/without RAM retention)
- Deep standby stop (selectable from with/without RAM retention)

Peripheral Clock Gating

The system can reduce the current consumption of the total system with gating the operation clocks of peripheral functions not used.

LQQ216



Note:

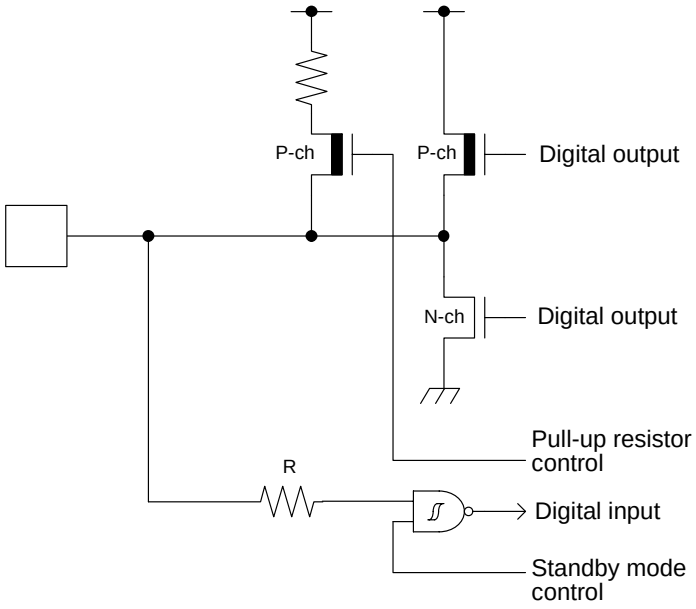
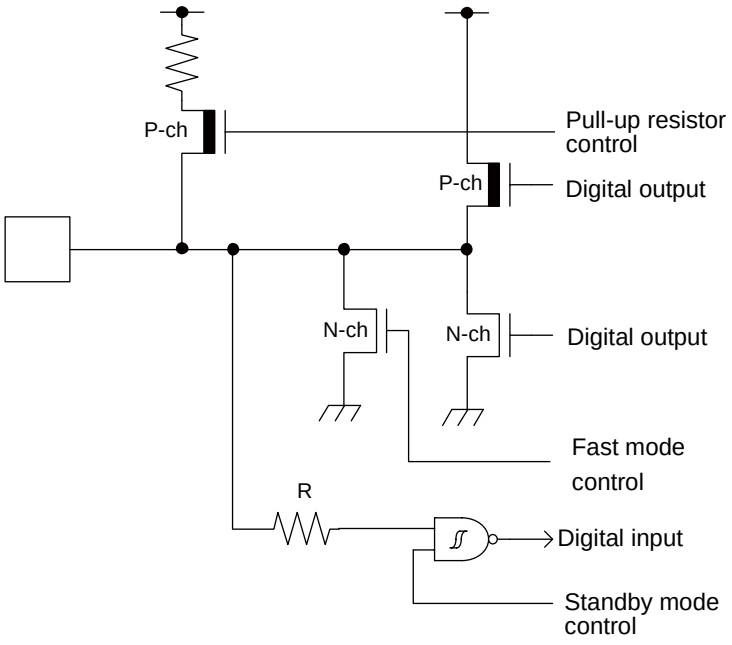
- *The number after the underscore ("_") in pin names such as XXX_1 and XXX_2 indicates the relocated port number. For these pins, there are multiple pins that provide the same function for the same channel. Use the extended port function register (EPFR) to select the pin.*

Pin No				Pin Name	I/O circuit type	Pin state type
LQQ216	LQP176	LQS144	LBE192			
25	20	17	G2	PAF SIN3_0 TIOB11_0 INT16_0 MADATA15_0	I	K
26	-	-	-	P58 SIN11_1 IC01_1 TIOB2_1 INT02_2 MADATA24_0	E	K
27	-	-	-	P59 SOT11_1 (SDA11_1) IC02_1 TIOB3_1 MADATA25_0	E	I
28	-	-	-	P5A SCK11_1 (SCL11_1) IC03_1 TIOB4_1 MADATA26_0	E	I
29	-	-	-	P5B FRCK0_1 TIOB5_1 MADATA27_0	E	I
30	21	18	G3	P08 SIN14_0 TIOB12_0 INT17_0 MDQM0_0	E	K
31	22	19	G4	P09 SOT14_0 (SDA14_0) TIOB13_0 INT18_0 MDQM1_0	E	K
32	23	20	G5	P0A ADTG_1 SCK14_0 (SCL14_0) AIN2_1 MCLKOUT_0	L	I

Pin No				Pin Name	I/O circuit type	Pin state type
LQQ216	LQP176	LQS144	LBE192			
33	-	-	-	P5C TIOA11_2 MADATA28_0 RTCCO_1 SUBOUT_1	E	I
34	24	-	G6	P30 RX0_1 TIOA13_2 INT03_2 MDQM2_0 I2SDI0_0	E	K
35	25	-	H4	P31 TX0_1 TIOB13_2 MDQM3_0 I2SCK0_0	E	I
36	26	21	H2	P32 BIN2_1 INT19_0 S_DATA1_0	L	K
37	27	22	J1	P33 FRCK0_0 ZIN2_1 S_DATA0_0	L	I
38	28	23	H3	P34 IC03_0 INT00_1 S_CLK_0	L	K
39	29	24	H1	VCC	-	-
40	30	25	H5	VSS	-	-
41	31	26	H6	P35 IC02_0 INT01_1 S_CMD_0	L	K
42	32	27	J5	P36 IC01_0 INT02_1 S_DATA3_0	L	K
43	33	28	J4	P37 IC00_0 INT03_1 S_DATA2_0	L	K

Pin No				Pin Name	I/O circuit type	Pin state type
LQQ216	LQP176	LQS144	LBE192			
77	62	54	M6	P49 VWAKEUP	O	U
78	63	-	K5	PF0 SCS63_0 RX2_1 FRCK1_1 TIOA15_1 INT22_1	E	K
79	64	-	K6	PF1 SCS62_0 TX2_1 TIOB15_1 INT23_1	E	K
80	65	55	L6	P70 ADTG_8 SIN1_1 INT06_0 MRDY_0	I	K
81	66	56	J6	P71 SOT1_1 (SDA1_1) MAD00_0	E	I
82	67	57	L8	P72 SIN9_0 TIOB0_0 INT07_0 MAD01_0	E	K
83	68	58	K8	P73 SOT9_0 (SDA9_0) TIOB1_0 MAD02_0	E	I
84	69	59	J8	P74 SCK9_0 (SCL9_0) TIOB2_0 MAD03_0	E	I
85	70	-	N8	PF2 RTO10_1 (PPG10_1) TIOA6_1 MRASX_0	L	I
86	71	-	M8	PF3 RTO11_1 (PPG10_1) TIOB6_1 INT05_1 MCASX_0	L	K
87	72	-	N9	PF4 RTO12_1 (PPG12_1) TIOA7_1 INT06_1 MSDWEX_0	L	K

Module	Pin name	Function	Pin No			
			LQQ 216	LQP 176	LQS 144	LBE 192
Multi-function serial 3	SIN3_0	Multi-function serial interface ch.3 input pin	25	20	17	G2
	SIN3_1		56	46	38	N2
	SOT3_0 (SDA3_0)	Multi-function serial interface ch.3 output pin. This pin operates as SOT3 when it is used in a UART/CSIO/LIN (operation modes 0 to 3) and as SDA3 when it is used in an I²C (operation mode 4).	24	19	16	F6
	SOT3_1 (SDA3_1)		57	47	39	N3
	SCK3_0 (SCL3_0)	Multi-function serial interface ch.3 clock I/O pin. This pin operates as SCK3 when it is used in a CSIO (operation modes 2) and as SCL3 when it is used in an I²C (operation mode 4).	23	18	15	F5
	SCK3_1 (SCL3_1)		58	48	40	M3
Multi-function serial 4	SIN4_0	Multi-function serial interface ch.4 input pin	212	172	140	B3
	SIN4_1		193	161	131	D7
	SOT4_0 (SDA4_0)	Multi-function serial interface ch.4 output pin. This pin operates as SOT4 when it is used in a UART/CSIO/LIN (operation modes 0 to 3) and as SDA4 when it is used in an I²C (operation mode 4).	211	171	139	C4
	SOT4_1 (SDA4_1)		192	160	130	A6
	SCK4_0 (SCL4_0)	Multi-function serial interface ch.4 clock I/O pin. This pin operates as SCK4 when it is used in a CSIO (operation modes 2) and as SCL4 when it is used in an I²C (operation mode 4).	210	170	138	B4
	SCK4_1 (SCL4_1)		198	166	136	D6
	CTS4_0	Multi-function serial interface ch.4 CTS input pin	208	168	-	B5
	CTS4_1		197	165	135	C6
	RTS4_0	Multi-function serial interface ch.4 RTS output pin	209	169	137	C5
	RTS4_1		194	162	132	E7
Multi-function serial 5	SIN5_0	Multi-function serial interface ch.5 input pin	147	121	97	F13
	SIN5_1		170	140	-	D11
	SOT5_0 (SDA5_0)	Multi-function serial interface ch.5 output pin. This pin operates as SOT5 when it is used in a UART/CSIO/LIN (operation modes 0 to 3) and as SDA5 when it is used in an I²C (operation mode 4).	146	120	96	F12
	SOT5_1 (SDA5_1)		171	141	-	B10
	SCK5_0 (SCL5_0)	Multi-function serial interface ch.5 clock I/O pin. This pin operates as SCK5 when it is used in a CSIO (operation modes 2) and as SCL5 when it is used in an I²C (operation mode 4).	145	119	95	F11
	SCK5_1 (SCL5_1)		172	142	-	C10
	CTS5_0	Multi-function serial interface ch.5 CTS input pin	144	118	94	F10
	CTS5_1		173	143	-	D10
	RTS5_0	Multi-function serial interface ch.5 RTS output pin	143	117	93	G9
	RTS5_1		174	144	-	B9

Type	Circuit	Remarks
L		・ CMOS level output ・ CMOS level hysteresis input ・ Pull-up resistor control ・ Standby mode control ・ Pull-up resistor: approximately 50 kΩ ・ I_{OH} = -8 mA, I_{OL} = 8 mA ・ When this pin is used as an I^2C pin, the digital output P-ch transistor is always off.
N		・ CMOS level output ・ CMOS level hysteresis input ・ 5V tolerant ・ Pull-up resistor control ・ Standby mode control ・ Pull-up resistor: approximately 50 kΩ ・ I_{OH} = -4 mA, I_{OL} = 4 mA (GPIO) ・ I_{OL} = 20mA (Fast mode Plus) ・ Available to control of PZR register (pseudo-open drain control) ・ For PZR registers, refer to GPIO in the “FM4 Family Peripheral Manual Main Part (002-04856)”. ・ When this pin is used as an I^2C pin, the digital output P-ch transistor is always off.

Surface Mount Type

Surface mount packaging has longer and thinner leads than lead-insertion packaging, and therefore leads are more easily deformed or bent. The use of packages with higher pin counts and narrower pin pitch results in increased susceptibility to open connections caused by deformed pins, or shorting due to solder bridges.

You must use appropriate mounting techniques. Cypress recommends the solder reflow method, and has established a ranking of mounting conditions for each product. Users are advised to mount packages in accordance with Cypress ranking of recommended conditions.

Lead-Free Packaging

CAUTION: When ball grid array (BGA) packages with Sn-Ag-Cu balls are mounted using Sn-Pb eutectic soldering, junction strength may be reduced under some conditions of use.

Storage of Semiconductor Devices

Because plastic chip packages are formed from plastic resins, exposure to natural environmental conditions will cause absorption of moisture. During mounting, the application of heat to a package that has absorbed moisture can cause surfaces to peel, reducing moisture resistance and causing packages to crack. To prevent this, do the following:

1. Avoid exposure to rapid temperature changes, which can cause moisture to condense inside the product. Store products in locations where temperature changes are slight.
2. Use dry boxes for product storage. Products should be stored below 70% relative humidity, and at temperatures between 5°C and 30°C.
3. When Dry Packages are opened, it is recommended to have humidity between 40% and 70%.
4. When necessary, Cypress packages semiconductor devices in highly moisture-resistant aluminum laminate bags, with a silica gel desiccant. Devices should be sealed in these aluminum laminate bags for storage.
5. Avoid storing packages where they are exposed to corrosive gases or high levels of dust.

Baking

Packages that have absorbed moisture may be de-moisturized by baking (heat drying). Follow the Cypress recommended conditions for baking.

Condition: 125°C/24 h

Static Electricity

Because semiconductor devices are particularly susceptible to damage by static electricity, you must take the following precautions:

1. Maintain relative humidity in the working environment between 40% and 70%. Use of an apparatus for ion generation may be needed to remove electricity.
2. Electrically ground all conveyors, solder vessels, soldering irons, and peripheral equipment.
3. Eliminate static body electricity by the use of rings or bracelets connected to ground through high resistance (on the level of 1 MΩ). Wearing of conductive clothing and shoes, and the use of conductive floor mats and other measures to minimize shock loads is recommended.
4. Ground all fixtures and instruments, or protect with anti-static measures.
5. Avoid the use of Styrofoam or other highly static-prone materials for storage of completed board assemblies.

Pin Status Type	Function Group	Power-On Reset or Low-Voltage Detection State	INITX Input State	Device Internal Reset State	Run mode or Sleep mode State	Timer mode, RTC mode, or Stop mode State		Deep Standby RTC mode or Deep Standby Stop mode State		Return From Deep Standby Mode State
		Power Supply Unstable	Power Supply Stable		Power Supply Stable	Power Supply Stable		Power Supply Stable		Power Supply Stable
		-	INITX=0	INITX=1	INITX=1	INITX=1		INITX=1		INITX=1
		-	-	-	-	SPL=0	SPL=1	SPL=0	SPL=1	-
F	NMIX selected	Setting disabled	Setting disabled	Setting disabled	Maintain previous state	Maintain previous state	Maintain previous state	WKUP input enabled	Hi-Z/ WKUP input enabled	Maintain previous state
	Resource other than above selected	Hi-Z	Hi-Z/ input enabled	Hi-Z/ input enabled			Hi-Z/ internal input fixed at 0			GPIO selected
	GPIO selected									
G	JTAG selected	Hi-Z	Pull-up/ input enabled	Pull-up/ input enabled	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state
	GPIO selected	Setting disabled	Setting disabled	Setting disabled			Hi-Z/ internal input fixed at 0	GPIO selected, internal input fixed at 0	Hi-Z/ internal input fixed at 0	GPIO selected
H	JTAG selected	Hi-Z	Pull-up/ input enabled	Pull-up/ input enabled	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state
	Resource other than above selected	Setting disabled	Setting disabled	Setting disabled			Hi-Z/Internal input fixed at 0	GPIO selected, internal input fixed at 0	Hi-Z/Internal input fixed at 0	GPIO selected
	GPIO selected									
I	Resource selected	Hi-Z	Hi-Z/ input enabled	Hi-Z/ input enabled	Maintain previous state	Maintain previous state	Hi-Z/Internal input fixed at 0	GPIO selected, internal input fixed at 0	Hi-Z/internal input fixed at 0	GPIO selected
	GPIO selected									

Pin Status Type	Function Group	Power-On Reset or Low-Voltage Detection State	INITX Input State	Device Internal Reset State	Run mode or Sleep mode State	Timer mode, RTC mode, or Stop mode State		Deep Standby RTC mode or Deep Standby Stop mode State		Return From Deep Standby Mode State
		Power Supply Unstable	Power Supply Stable		Power Supply Stable	Power Supply Stable		Power Supply Stable		Power Supply Stable
		-	INITX=0	INITX=1	INITX=1	INITX=1		INITX=1		INITX=1
		-	-	-	-	SPL=0	SPL=1	SPL=0	SPL=1	-
O	Analog input selected	Hi-Z	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled
	Trace selected	Setting disabled	Setting disabled	Setting disabled	Maintain previous state	Maintain previous state	Trace output	GPIO selected, internal input fixed at 0	Hi-Z/internal input fixed at 0	GPIO selected
	External interrupt enable selected						Maintain previous state			
	Resource other than above selected						Hi-Z/internal input fixed at 0			
	GPIO selected									
P	Analog input selected	Hi-Z	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled
	WKUP enabled	Setting disabled	Setting disabled	Setting disabled	Maintain previous state	Maintain previous state	Maintain previous state	WKUP input enabled	Hi-Z/ WKUP input enabled	GPIO selected
	Resource other than above selected						Hi-Z/internal input fixed at 0	GPIO selected, internal input fixed at 0	Hi-Z/internal input fixed at 0	
	GPIO selected									

Table 12-9 Typical and Maximum Current Consumption in Deep Standby Stop Mode, Deep Standby RTC Mode and VBAT

Parameter	Symbol	Pin Name	Conditions	Frequency	Value		Unit	Remarks
					Typ*1	Max*2		
Power supply current	I_{CCHD}	VCC	Deep standby Stop mode (When RAM is off)	-	96	248	µA	*3, *4 T_A = +25°C
					-	3009	µA	*3, *4 T_A = +85°C
					-	3889	µA	*3, *4 T_A = +105°C
			Deep standby Stop mode (When RAM is on)	-	106	259	µA	*3, *4 T_A = +25°C
					-	3020	µA	*3, *4 T_A = +85°C
					-	3900	µA	*3, *4 T_A = +105°C
	I_{CCRD}		Deep standby RTC mode (When RAM is off)	32 kHz	96	248	µA	*3, *4 T_A = +25°C
					-	3009	µA	*3, *4 T_A = +85°C
					-	3889	µA	*3, *4 T_A = +105°C
			Deep standby RTC mode (When RAM is on)		106	259	µA	*3, *4 T_A = +25°C
					-	3020	µA	*3, *4 T_A = +85°C
					-	3900	µA	*3, *4 T_A = +105°C
	I_{CCVBAT}	VBAT	RTC stop*6	-	0.0058	0.1	µA	*3, *4, *5 T_A = +25°C
					-	1.4	µA	*3, *4, *5 T_A = +85°C
					-	3.3	µA	*3, *4, *5 T_A = +105°C
			RTC operation*6		1.0	1.8	µA	*3, *4 T_A = +25°C
					-	3.2	µA	*3, *4 T_A = +85°C
					-	5.1	µA	*3, *4 T_A = +105°C

*1: V_{CC} = 3.3 V

*2: V_{CC} = 5.5 V

*3: When all ports are fixed

*4: When LVD is off

*5: When sub oscillation is off

*6: In the case of setting RTC after VCC power on

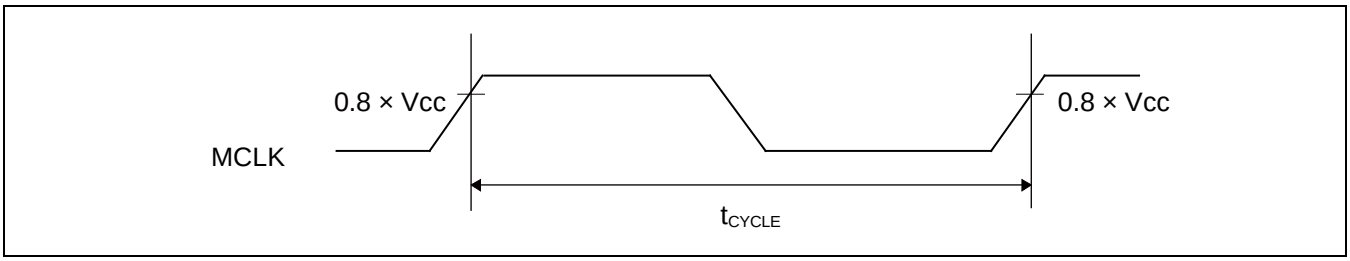
12.4.10 External Bus Timing

External Bus Clock Output Characteristics

Parameter	Symbol	Pin Name	Conditions	Value		Unit	Remarks
				Min	Typ		
Output frequency	t_{CYCLE}	MCLKOUT *1		-	50 *2	MHz	

*1: The external bus clock (MCLKOUT) is a divided clock of HCLK.
For more information about setting of clock divider, see Chapter 14: External Bus Interface in FM4 Family Peripheral Manual Main Part (002-04856).

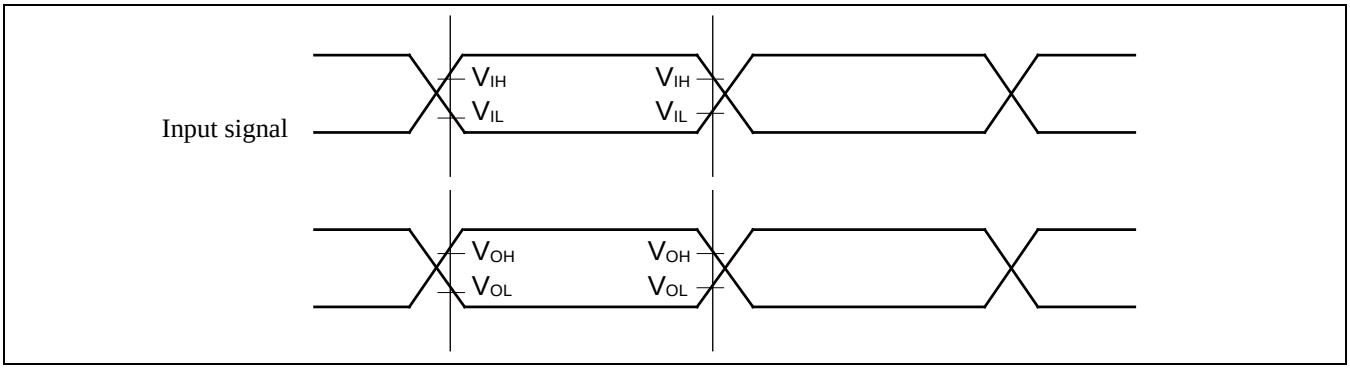
*2: Generate MCLKOUT at setting more than four divisions when the AHB bus clock exceeds 100 MHz.



External Bus Signal I/O Characteristics

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

Parameter	Symbol	Conditions	Value	Unit	Remarks
Signal input characteristics	V_{IH}	-	0.8 × V_{CC}	V	
	V_{IL}		0.2 × V_{CC}	V	
Signal output characteristics	V_{OH}		0.8 × V_{CC}	V	
	V_{OL}		0.2 × V_{CC}	V	



When Using Synchronous Serial Chip Select (SCINV = 1, CSLVL = 0)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

Parameter	Symbol	Conditions	V_{CC} < 4.5 V		V_{CC} ≥ 4.5 V		Units
			Min	Max	Min	Max	
SCS ↑ →SCK ↑ setup time	t_{CSSI}	Internal shift clock operation	(*1)-50	(*1)+0	(*1)-50	(*1)+0	ns
SCK ↓ →SCS ↓ hold time	t_{CSHI}		(*2)+0	(*2)+50	(*2)+0	(*2)+50	ns
SCS deselect time	t_{CSDI}		(*3)-50 +5t_{CYCP}	(*3)+50 +5t_{CYCP}	(*3)-50 +5t_{CYCP}	(*3)+50 +5t_{CYCP}	ns
SCS ↑ →SCK ↑ setup time	t_{CSSE}	External shift clock operation	3t_{CYCP}+30	-	3t_{CYCP}+30	-	ns
SCK ↓ →SCS ↓ hold time	t_{CSHE}		0	-	0	-	ns
SCS deselect time	t_{CSDE}		3t_{CYCP}+30	-	3t_{CYCP}+30	-	ns
SCS ↑ →SOT delay time	t_{DSE}		-	40	-	40	ns
SCS ↓ →SOT delay time	t_{DEE}		0	-	0	-	ns

(*1): CSSU bit value×serial chip select timing operating clock cycle [ns]

(*2): CSHD bit value×serial chip select timing operating clock cycle [ns]

(*3): CSDS bit value×serial chip select timing operating clock cycle [ns]

Notes:

- *t_{CYCP} indicates the APB bus clock cycle time. For more information about the APB bus number to which the multi-function serial is connected, see 8. Block Diagram in this data sheet.*
- *For more information about CSSU, CSHD, CSDS, and the serial chip select timing operating clock, see FM4 Family Peripheral Manual Main Part (002-04856).*
- *When the external load capacitance C_L = 30 pF.*

High-Speed Synchronous Serial (SPI = 1, SCINV = 0)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

Parameter	Symbol	Pin Name	Conditions	V_{CC} < 4.5 V		V_{CC} ≥ 4.5 V		Unit
				Min	Max	Min	Max	
Serial clock cycle time	t_{SCYC}	SCKx	Internal shift clock operation	$4t_{CYCP}$	-	$4t_{CYCP}$	-	ns
SCK↑→SOT delay time	t_{SHOVI}	SCKx, SOTx		- 10	+ 10	- 10	+ 10	ns
SIN→SCK↓ setup time	t_{IVSLI}	SCKx, SINx		14 12.5*	-	12.5	-	ns
SCK↓→SIN hold time	t_{SLIXI}	SCKx, SINx		5	-	5	-	ns
SOT→SCK↓ delay time	t_{SOVLI}	SCKx, SOTx		$2t_{CYCP}$ - 10	-	$2t_{CYCP}$ - 10	-	ns
Serial clock L pulse width	t_{SLSH}	SCKx	External shift clock operation	$2t_{CYCP}$ - 5	-	$2t_{CYCP}$ - 5	-	ns
Serial clock H pulse width	t_{SHSL}	SCKx		t_{CYCP} + 10	-	t_{CYCP} + 10	-	ns
SCK↑→SOT delay time	t_{SHOVE}	SCKx, SOTx		-	15	-	15	ns
SIN→SCK↓ setup time	t_{IVSLE}	SCKx, SINx		5	-	5	-	ns
SCK↓→SIN hold time	t_{SLIXE}	SCKx, SINx		5	-	5	-	ns
SCK fall time	t_F	SCKx		-	5	-	5	ns
SCK rise time	t_R	SCKx		-	5	-	5	ns

Notes:

- *The above characteristics apply to CLK synchronous mode.*
- *t_{CYCP} indicates the APB bus clock cycle time. For more information about the APB bus number to which the multi-function serial is connected, see 8. Block Diagram in this data sheet.*
- *These characteristics only guarantee the following pins:*

  No chip select: SIN4_0, SOT4_0, SCK4_0

  Chip select: SIN6_0, SOT6_0, SCK6_0, SCS60_0, SCS61_0, SCS62_0, SCS63_0
- *When the external load capacitance C_L = 30 pF. (for *, when C_L = 10 pF)*

High-Speed Synchronous Serial (SPI = 1, SCINV = 1)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

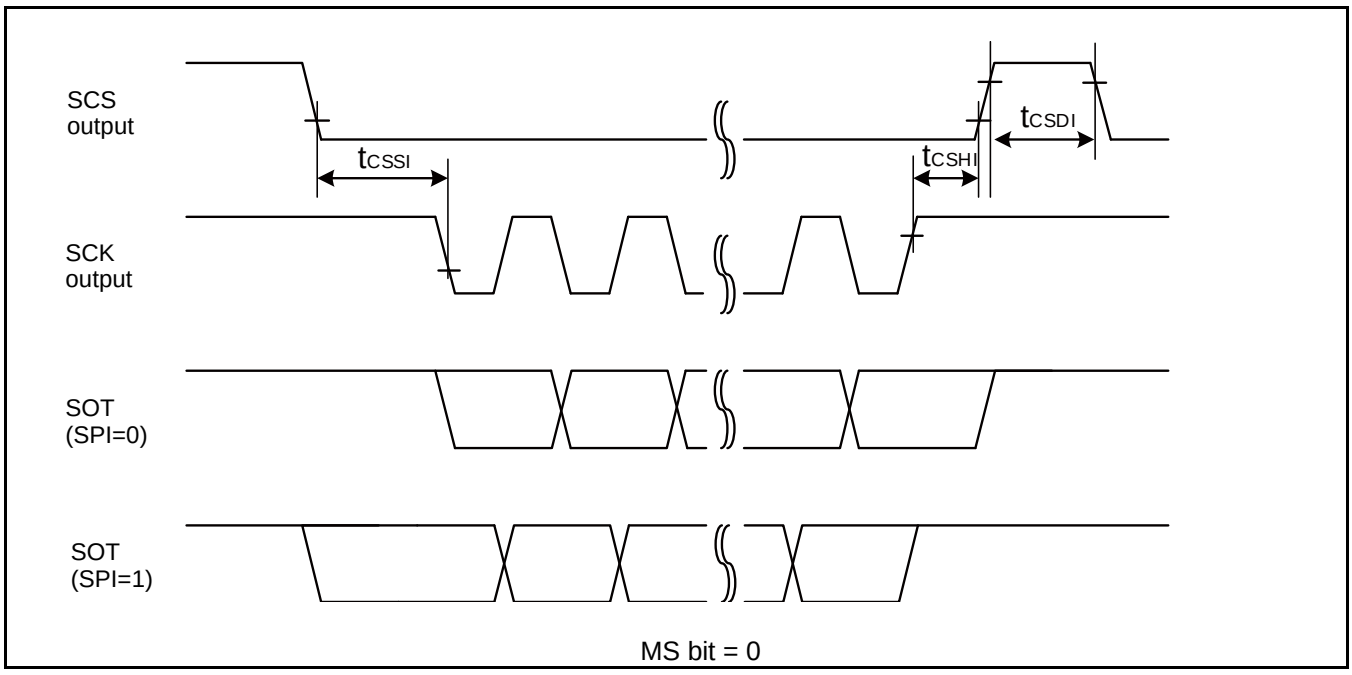
Parameter	Symbol	Pin Name	Conditions	V_{CC} < 4.5 V		V_{CC} ≥4.5 V		Unit
				Min	Max	Min	Max	
Serial clock cycle time	t_{SCYC}	SCKx	Internal shift clock operation	$4t_{CYCP}$	-	$4t_{CYCP}$	-	ns
SCK↓→SOT delay time	t_{SLOVI}	SCKx, SOTx		- 10	+ 10	- 10	+ 10	ns
SIN→SCK↑ setup time	t_{IVSHI}	SCKx, SINx		14 12.5*	-	12.5	-	ns
SCK↑→SIN hold time	t_{SHIXI}	SCKx, SINx		5	-	5	-	ns
SOT→SCK↑ delay time	t_{SOVHI}	SCKx, SOTx		$2t_{CYCP}$ - 10	-	$2t_{CYCP}$ - 10	-	ns
Serial clock L pulse width	t_{SLSH}	SCKx	External shift clock operation	$2t_{CYCP}$ - 5	-	$2t_{CYCP}$ - 5	-	ns
Serial clock H pulse width	t_{SHSL}	SCKx		t_{CYCP} + 10	-	t_{CYCP} + 10	-	ns
SCK↓→SOT delay time	t_{SLOVE}	SCKx, SOTx		-	15	-	15	ns
SIN→SCK↑ setup time	t_{IVSHE}	SCKx, SINx		5	-	5	-	ns
SCK↑→SIN hold time	t_{SHIXE}	SCKx, SINx		5	-	5	-	ns
SCK fall time	t_F	SCKx		-	5	-	5	ns
SCK rise time	t_R	SCKx		-	5	-	5	ns

Notes:

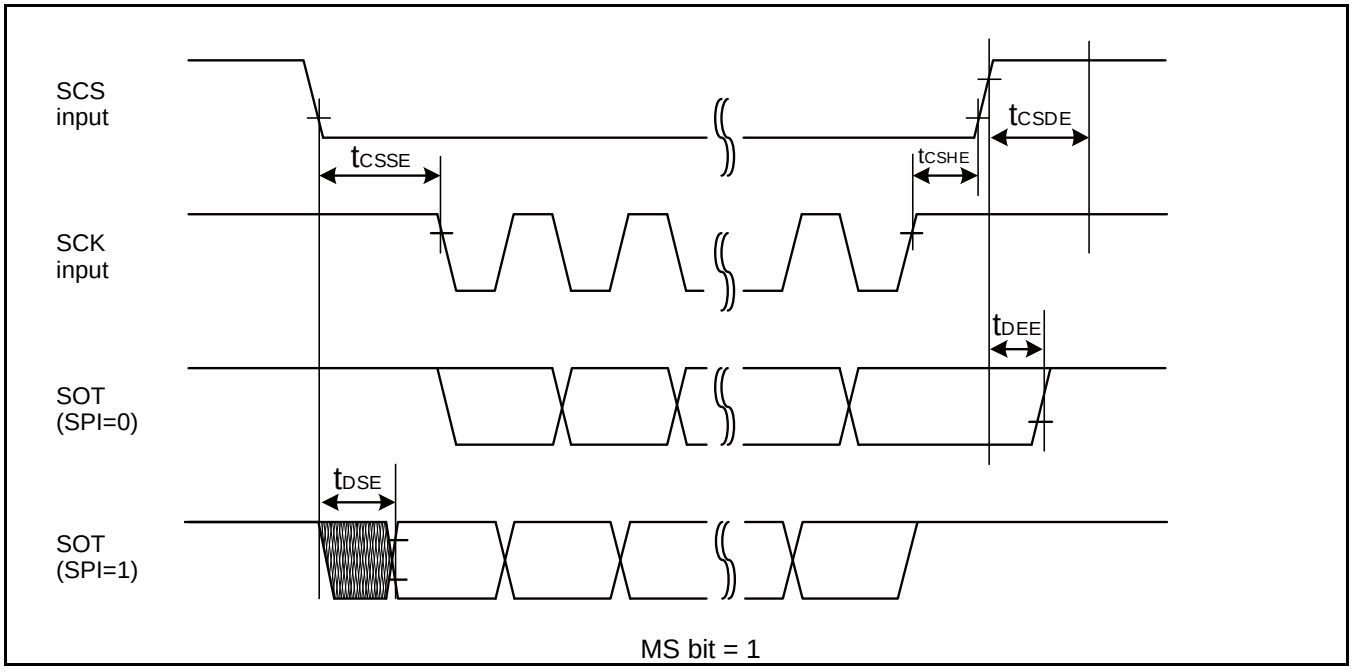
- *The above characteristics apply to CLK synchronous mode.*
- *t_{CYCP} indicates the APB bus clock cycle time. For more information about the APB bus number to which the multi-function serial is connected, see 8. Block Diagram in this data sheet.*
- *These characteristics only guarantee the following pins:*

  No chip select: SIN4_0, SOT4_0, SCK4_0

  Chip select: SIN6_0, SOT6_0, SCK6_0, SCS60_0, SCS61_0, SCS62_0, SCS63_0
- *When the external load capacitance C_L = 30 pF. (for *, when C_L = 10 pF)*



MS bit = 0



MS bit = 1

Fast Mode Plus (Fm+)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

Parameter	Symbol	Conditions	Fast Mode Plus (Fm+)*6		Unit	Remarks
			Min	Max		
SCL clock frequency	f_{SCL}	C_L = 30 pF, R = (V_p/I_{OL})*1	0	1000	kHz	
(Repeated) START condition hold time SDA ↓ → SCL ↓	t_{HDSTA}		0.26	-	µs	
SCL clock L width	t_{LOW}		0.5	-	µs	
SCL clock H width	t_{HIGH}		0.26	-	µs	
SCL clock frequency	t_{SUSTA}		0.26	-	µs	
(Repeated) START condition hold time SDA ↓ → SCL ↓	t_{HDDAT}		0	0.45*2, *3	µs	
Data setup time SDA ↓ ↑ → SCL ↑	t_{SUDAT}		50	-	ns	
Stop condition setup time SCL ↑ → SDA ↑	t_{SUSTO}		0.26	-	µs	
Bus free time between "Stop condition" and "START condition"	t_{BUF}		0.5	-	µs	
Noise filter	t_{SP}	60 MHz ≤ t_{CYCP} < 80 MHz	6 t_{CYCP}*4	-	ns	*5
		80 MHz ≤ t_{CYCP} ≤100 MHz	8 t_{CYCP}*4	-	ns	

*1: R and C_L represent the pull-up resistance and load capacitance of the SCL and SDA lines, respectively. V_p indicates the power supply voltage of the pull-up resistance and I_{OL} indicates V_{OL} guaranteed current.

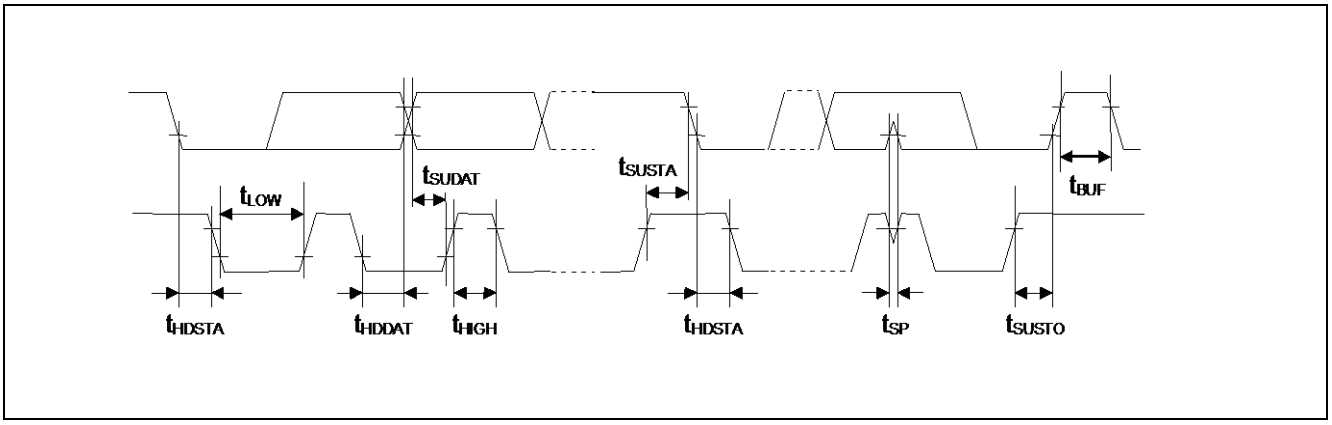
*2: The maximum t_{HDDT} must not extend beyond the low period (t_{LOW}) of the device's SCL signal.

*3: The Fast mode I^2C bus device can be used on a Standard-mode I^2C bus system as long as the device satisfies the requirement of "t_{SUDAT} ≥ 250 ns."

*4: t_{CYCP} is the APB bus clock cycle time. For more information about the APB bus number to which the I^2C is connected, see "8.Block Diagram" in this data sheet.
To use fast mode plus (Fm+), set the peripheral bus clock at 64 MHz or more.

*5: The noise filter time can be changed by register settings. Change the number of the noise filter steps according to the APB bus clock frequency.

*6: When using fast mode plus (Fm+), set the I/O pin to the mode corresponding to I^2C Fm+ in the EPFR register.
See Chapter12: I/O PORT in FM4 Family Peripheral Manual Main Part (002-04856) for the details.



12.8 MainFlash Memory Write/Erase Characteristics

(V_{CC} = 2.7V to 5.5V)

Parameter		Value			Unit	Remarks
		Min	Typ	Max		
Sector erase time	Large Sector	-	0.7	3.7	s	Includes write time prior to internal erase
	Small Sector	-	0.3	1.1	s	
Half word (16-bit) write time	Write cycles ≤ 100 times	-	12	100	µs	Not including system-level overhead time
	Write cycles > 100 times			200		
Chip erase time*		-	13.6	68	s	Includes write time prior to internal erase

*: It indicates the chip erase time of 1MB MainFlash memory

For devices with 1.5 MB or 2 MB of MainFlash memory, two erase cycles are required.

See 3.2.2 Command Operating Explanations and 3.3.3 Flash Erase Operation in this product's Flash Programming Manual for the detail.

Write Cycles and Data Retention Time

Erase/Write Cycles (Cycle)	Data Retention Time (Year)
1,000	20*
10,000	10*
100,000	5*

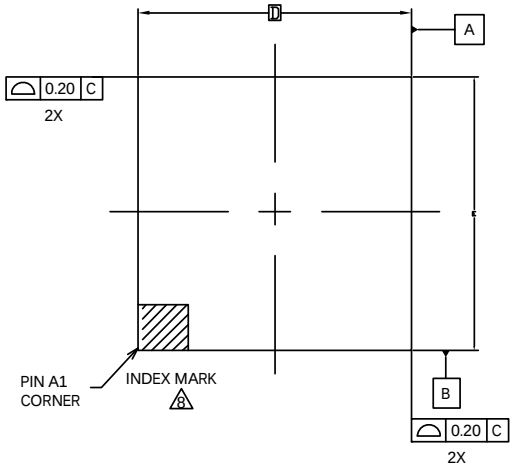
*: This value comes from the technology qualification (using Arrhenius equation to translate high temperature acceleration test result into average temperature value at + 85°C).

12.9 Dual Flash Memory Write/Erase Characteristics

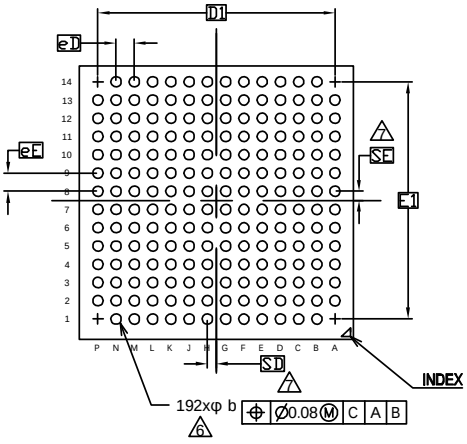
It is the same write/erase characteristics as the MainFlash memory.

See 3.6 Dual flash mode in this product's Flash Programming Manual for the detail of dual flash mode.

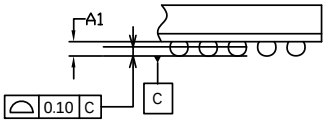
Package Type	Package Code
PFBGA 192	LBE 192



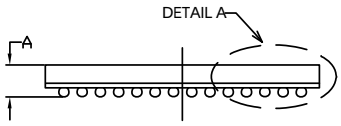
TOP VIEW



BOTTOM VIEW



DETAIL A



SIDE VIEW

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	——	——	1.45
A1	0.25	0.35	0.45
D	12.00 BSC		
E	12.00 BSC		
D1	10.40 BSC		
E 1	10.40 BSC		
MD	14		
ME	14		
n	192		
Φb	0.35	0.45	0.55
eD	0.80 BSC		
eE	0.80 BSC		
SD / SE	0.40 BSC		

NOTES

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONS AND TOLERANCES METHODS PER ASME Y14.5-2009. THIS OUTLINE CONFORMS TO JEP95, SECTION 4.5.
3. BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-010.
4. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION. SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION. n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
7. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW. WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" OR "SE" =0. WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
8. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK. METALLIZED MARK INDENTATION OR OTHER MEANS.
9. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

002-13493 **

PACKAGE OUTLINE, 192 BALL FBGA
12.00X12.00X1.45 MM LBE192 REV**